Supporting Information

High thermoelectric performances of SnSe allotropes

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Fig. S1 Schematic structure of bonds and angles for the five optimized SnSe monolayer polymorphs.

Phases	R1	R2	R3	R4	R5	R6	θ1	θ2	θ3	θ4	θ5	θ6
α-SnSe	2.60	2.88	-	-	-	-	94.28	104.77	92.80	-	-	-
β- SnSe	2.66	-	-	-	-	-	90.19	-	-	-	-	-
γ- SnSe	3.05	2.62	-	-	-	-	100.78	92.30	90.23	-	-	-
δ- SnSe	2.81	2.79	2.64	-	-	-	102.17	93.30	93.49	103.27	-	-
ε- SnSe	2.69	2.65	2.69	2.69	2.69	2.65	96.13	122.52	101.28	100.95	87.66	79.1
												1

Table. S1 The detailed parameters of bonds and angles for the five optimized SnSe monolayer polymorphs.



Fig. S2 The evolution of the total potential energy with simulation time of α -SnSe, β -SnSe, γ -SnSe, δ -SnSe and ϵ -SnSe single-layer during ab initio molecular dynamics simulations and the snapshots of the final atomic configurations at 300K.

Table S2. The calculated elastic constants (C_{ij}), bulk modulus (B), shear modulus (G), density (ρ), volume (V), transverse sound velocity (v_s), longitudinal sound velocity (v_l), , and minimum lattice thermal conductivity (κ_{min}) of α -SnSe, β -SnSe, γ -SnSe, δ -SnSe and ϵ -SnSe.

Phases	C ₁₁ (Gpa)	C ₁₂ (Gpa)	C ₄₄ (Gpa)	ρ(g/cm ³)	V (Å ³)	B(Gpa)	G(Gpa)	V _s (m/s)	V _l (m/s)	κ _{min}
α	20.9	4.42	3.57	6.66	49.31	9.91	5.44	1886	3349	0.175
ß	15 7	11 20	5 17	7 52	21.86	12 76	3.08	1861	3065	0 156
р	13.7	11.29	5.17	1.52	21.00	12.70	5.98	1801	3903	0.150
γ	34.80	4.31	3.92	7.72	42.50	14.47	8.45	2254	3934	0.219
δ	15.49	5.22	5.20	6.64	99.07	8.64	5.174	2087	3618	0.162
3	17.43	9.18	7.83	7.55	87.16	11.93	6.35	2222	3982	0.184

Table. S3 The detailed parameters of effective masses at VBM, VBM1, CBM, CBM1 and Seebeck coefficient with the carrier concentration of 5×10^{19} cm⁻³ at 300 K for the five optimized SnSe monolayer polymorphs.

Phases	m*(m0)	m*(m0)	m*(m0)	m*(m0)	Seebeck coefficient
	VBM	CBM	VBM1	CBM1	$(\mu V/K)$
α	0.15	0.17	0.17	0.23	66.37
β	1.15	1.10	1.36	0.45	348
γ	1.07	0.11	0.18	0.04	325
δ	0.29	0.71	0.07	0.07	71.32
3	1.15	0.93	1.68	0.23	265



Fig. S3 Thermoelectric properties as a function of temperature from 300K to 800K for holedoped SnSe crystals. (a) Electrical conductivity. (b) Seebeck coefficient. (c)Power factor (PF). (d) Total thermal conductivity. (e) ZT values for α -SnSe.



Fig. S4 Thermoelectric properties as a function of temperature from 300K to 800K for holedoped SnSe crystals. (a) Electrical conductivity. (b) Seebeck coefficient. (c)Power factor (PF). (d) Total thermal conductivity. (e) ZT values for β -SnSe.



Fig. S5 Thermoelectric properties as a function of temperature from 300K to 800K for holedoped SnSe crystals. (a) Electrical conductivity. (b) Seebeck coefficient. (c)Power factor (PF). (d) Total thermal conductivity. (e) ZT values for γ -SnSe.



Fig. S6 Thermoelectric properties as a function of temperature from 300K to 800K for holedoped SnSe crystals. (a) Electrical conductivity. (b) Seebeck coefficient. (c)Power factor (PF). (d) Total thermal conductivity. (e) ZT values for δ -SnSe.



Fig. S7 Thermoelectric properties as a function of temperature from 300K to 800K for holedoped SnSe crystals. (a) Electrical conductivity. (b) Seebeck coefficient. (c)Power factor (PF). (d) Total thermal conductivity. (e) ZT values for ε -SnSe.

Crystal Coordinate Lists:

1. alpha.cif

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3. gamma.cif

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5. epsilon.cif

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